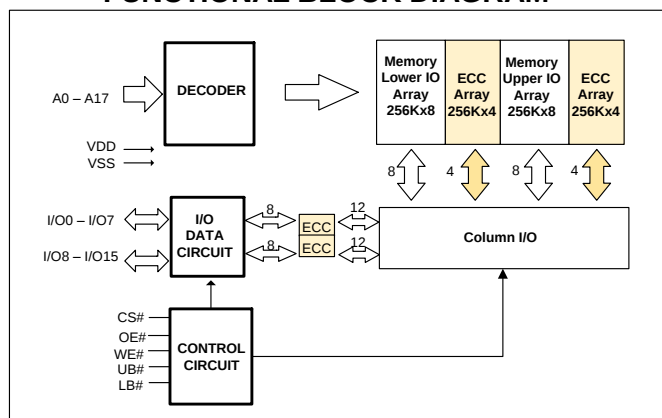


256Kx16 HIGH SPEED ASYNCHRONOUS CMOS STATIC RAM with ECC

KEY FEATURES

- High-speed access time: 20ns
- Single power supply
 - 1.65V-2.2V VDD
- Low Standby Current: 1.5mA (typical)
- Fully static operation: no clock or refresh required
- Data control
- Three state outputs
- Industrial and Automotive temperature support
- Lead-free available
- Error Detection and Correction

FUNCTIONAL BLOCK DIAGRAM



DESCRIPTION

The ISSI IS61WV25616EDALL are high-speed, low power, 4M bit static RAMs organized as 256K words by 16 bits. It is fabricated using ISSI's high-performance CMOS technology and implemented ECC function to improve reliability.

When CS# is HIGH (deselected), the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs. The active LOW Write Enable (WE#) controls both writing and reading of the memory.

A data byte allows Upper Byte (UB#) and Lower Byte (LB#) access.

The IS61WV25616EDALL are packaged in the JEDEC standard 48-pin mini BGA (6mm x 8mm), and 44-pin TSOP (TYPE II)

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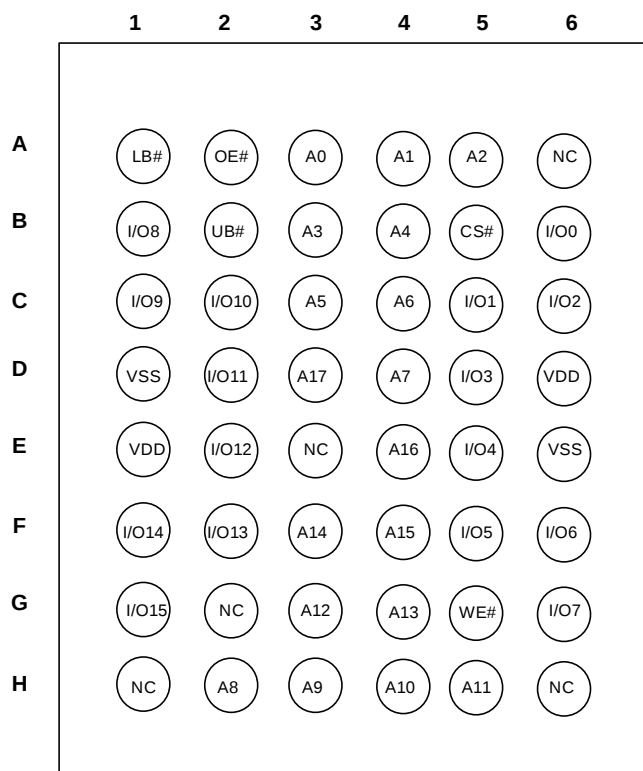
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- the risk of injury or damage has been minimized;
- the user assume all such risks; and
- potential liability of Integrated Silicon Solution, Inc is adequately protected under the circumstances

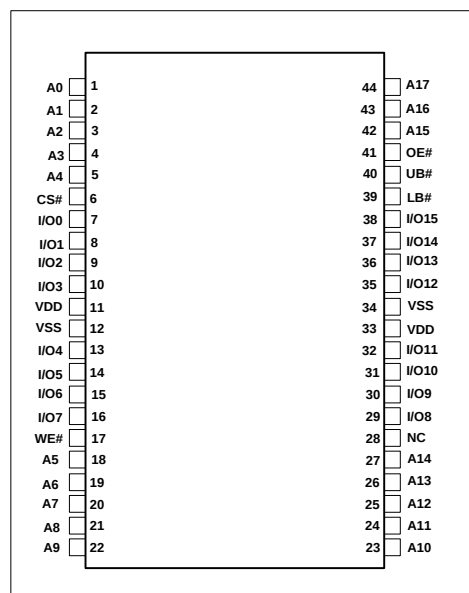
IS61WV25616EDALL

PIN CONFIGURATIONS

48-Pin mini BGA(6mm x 8mm)



44-Pin TSOP-II



PIN DESCRIPTIONS

A0-A17	Address Inputs
I/O0-I/O15	Data Inputs/Outputs
CS#	Chip Enable Input
OE#	Output Enable Input
WE#	Write Enable Input
LB#	Lower-byte Control (I/O0-I/O7)
UB#	Upper-byte Control (I/O8-I/O15)
NC	No Connection
VDD	Power
VSS	Ground

FUNCTION DESCRIPTION

SRAM is one of random access memories. Each byte or word has an address and can be accessed randomly. SRAM has various modes supported. Each function is described below with Truth Table.

STANDBY MODE

Device enters standby mode when deselected (CS# HIGH). The input and output pins (I/O0-15) are placed in a high impedance state. The current consumption in this mode will be ISB1, or ISB2.

WRITE MODE

Write operation issues with Chip Select (CS#) Low and Write Enable (WE#) Low. The input and output pins (I/O0-15) are in data input mode. Output buffers are closed during this time even if OE# is Low. UB# and LB# enables a byte write feature. By enabling LB# Low, data from I/O pins (I/O0 through I/O7) are written into the location specified on the address pins. And with UB# being Low, data from I/O pins (I/O8 through I/O15) are written into the location.

READ MODE

Read operation issues with Chip Select (CS#) Low and Write Enable (WE#) High. When OE# is Low, output buffer turns on to make data output. Any input to I/O pins during READ mode is not permitted. UB# and LB# enables a byte read feature. By enabling LB# Low, data from memory appears on I/O0-7. And with UB# being Low, data from memory appears on I/O8-15.

In the READ mode, output buffers can be turned off by pulling OE# High. In this mode, internal device operates as READ but I/Os are in a high impedance state. Since device is in READ mode, active current is used.

TRUTH TABLE

Mode	CS#	WE#	OE#	LB#	UB#	I/O0-I/O7	I/O8-I/O15	VDD Current
Not Selected	H	X	X	X	X	High-Z	High-Z	ISB1, ISB2
Output Disabled	L	H	H	L	X	High-Z	High-Z	ICC, ICC1
	L	X	X	H	H	High-Z	High-Z	
Read	L	H	L	L	H	DOUT	High-Z	ICC, ICC1
	L	H	L	H	L	High-Z	DOUT	
	L	H	L	L	L	DOUT	DOUT	
Write	L	L	X	L	H	DIN	High-Z	ICC, ICC1
	L	L	X	H	L	High-Z	DIN	
	L	L	X	L	L	DIN	DIN	

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
V _{term}	Terminal Voltage with Respect to VSS	−0.5 to V _{DD} + 0.5V	V
V _{DD}	V _{DD} Related to VSS	−0.3 to 4.0	V
t _{Stg}	Storage Temperature	−65 to +150	°C
P _T	Power Dissipation	1.0	W

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

PIN CAPACITANCE⁽¹⁾

Parameter	Symbol	Test Condition	Max	Units
Input capacitance	C _{IN}	T _A = 25°C, f = 1 MHz, V _{DD} = V _{DD} (typ)	6	pF
DQ capacitance (IO0–IO15)	C _{I/O}		8	pF

Note:

1. These parameters are guaranteed by design and tested by a sample basis only.

OPERATING RANGE⁽¹⁾

Range	Ambient Temperature	PART NUMBER	SPEED (MAX)	VDD
Commercial	0°C to +70°C	IS61WV25616EDALL	20 ns	1.65V – 2.2V
Industrial	−40°C to +85°C		20 ns	1.65V – 2.2V

Note:

1. Full device AC operation assumes a 100 μs ramp time from 0 to V_{DD}(min) and 200 μs wait time after V_{DD} stabilization.

THERMAL CHARACTERISTICS⁽¹⁾

Parameter	Symbol	Rating	Units
Thermal resistance from junction to ambient (airflow = 1m/s)	R _{θJA}	TBD	°C/W
Thermal resistance from junction to pins	R _{θJB}	TBD	°C/W
Thermal resistance from junction to case	R _{θJC}	TBD	°C/W

Note:

1. These parameters are guaranteed by design and tested by a sample basis only.

AC TEST CONDITIONS (OVER THE OPERATING RANGE)

Parameter	Unit (1.65V~2.2V)
Input Pulse Level	0V to V_{DD}
Input Rise and Fall Time	1.5 ns
Output Timing Reference Level	0.9V
R1 (ohm)	13500
R2 (ohm)	10800
V_{TM} (V)	1.8V
Output Load Conditions	Refer to Figure 1 and 2

OUTPUT LOAD CONDITIONS FIGURES

FIGURE 1

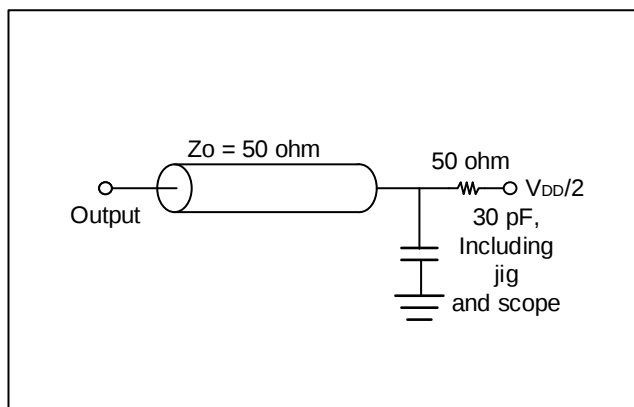
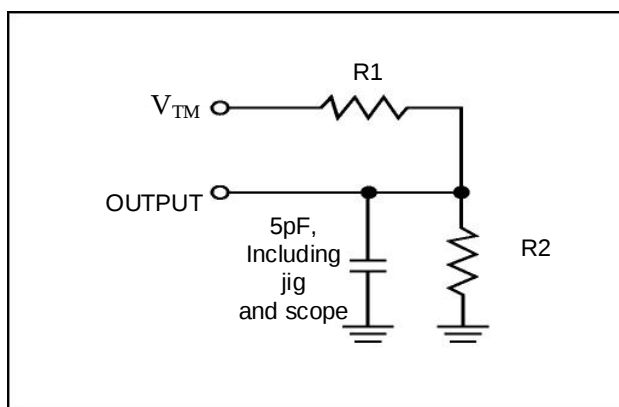


FIGURE 2



IS61WV25616EDALL

DC ELECTRICAL CHARACTERISTICS

IS61(64)WV25616EEBLL DC ELECTRICAL CHARACTERISTICS-I (OVER THE OPERATING RANGE) VDD = 1.65V – 2.2V

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	I _{OH} = -0.1 mA	1.4	—	V
V _{OL}	Output LOW Voltage	I _{OL} = 0.1 mA	—	0.2	V
V _{IH} (1)	Input HIGH Voltage		1.4	V _{DD} + 0.2	V
V _{IL} (1)	Input LOW Voltage		-0.2	0.4	V
I _{LI}	Input Leakage	GND < V _{IN} < V _{DD}	-1	1	μA
I _{LO}	Output Leakage	GND < V _{IN} < V _{DD} , Output Disabled	-1	1	μA

Notes:

1. V_{ILL}(min) = -1.0V AC (pulse width < 20ns). Not 100% tested.
2. V_{IIH}(max) = V_{DD} + 1.0V AC (pulse width < 20ns). Not 100% tested.

POWER SUPPLY CHARACTERISTICS-II FOR POWER (OVER THE OPERATING RANGE)

Symbol	Parameter	Test Conditions	Grade	-20 Max	Unit
ICC	V _{DD} Dynamic Operating Supply Current	V _{DD} = MAX, I _{OUT} = 0 mA, f = f _{MAX}	Com.	25	mA
			Ind.	30	
			Auto.	-	
ICC1	Operating Supply Current	V _{DD} = MAX, I _{OUT} = 0 mA, f = 0	Com.	20	mA
			Ind.	25	
			Auto.	-	
ISB1	TTL Standby Current (TTL Inputs)	V _{DD} = MAX, V _{IN} = V _{IH} or V _{IL} , CS# ≥ V _{IH} , f = 0	Com.	10	mA
			Ind.	15	
			Auto.	-	
ISB2	CMOS Standby Current (CMOS Inputs)	V _{DD} = MAX, CS# ≥ V _{DD} - 0.2V, V _{IN} ≥ V _{DD} - 0.2V, or V _{IN} ≤ 0.2V, f = 0	Com.	5	mA
			Ind.	6	
			Auto.	-	
			Typ. (2)	1.5	

Notes:

1. At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input line change.
2. Typical values are measured at V_{DD} = 1.8V, T_A = 25 °C and not 100% tested.

AC CHARACTERISTICS (OVER OPERATING RANGE)

READ CYCLE AC CHARACTERISTICS

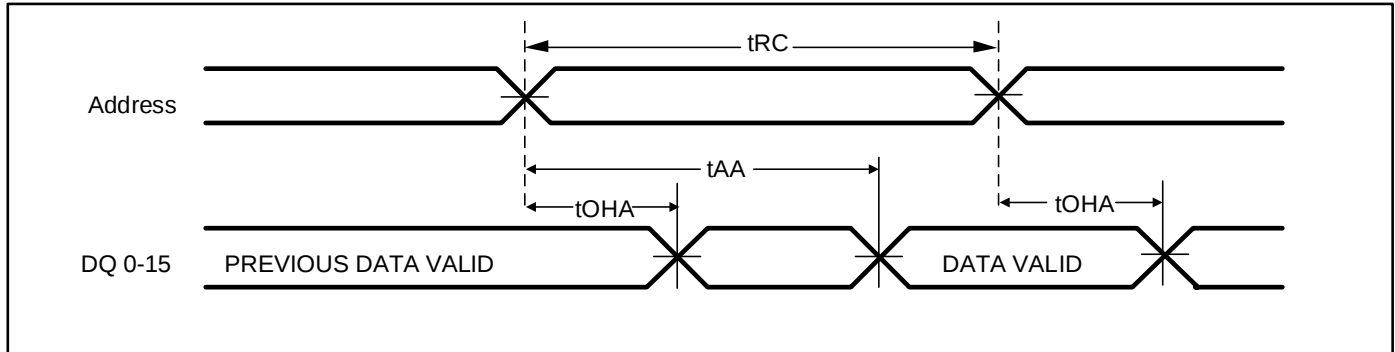
Parameter	Symbol	-20 ⁽¹⁾		unit	notes
		Min	Max		
Read Cycle Time	tRC	20	-	ns	
Address Access Time	tAA	-	20	ns	
Output Hold Time	tOHA	2.5	-	ns	
CS# Access Time	tACE	-	20	ns	
OE# Access Time	tDOE	-	8	ns	
OE# to High-Z Output	tHZOE	0	8	ns	2
OE# to Low-Z Output	tLZOE	0	-	ns	2
CS# to High-Z Output	tHZCE	0	8	ns	2
CS# to Low-Z Output	tLZCE	3	-	ns	2
UB#, LB# Access Time	tBA	-	8	ns	
UB#, LB# to High-Z Output	tHZB	0	8	ns	2
UB#, LB# to Low-Z Output	tLZB	0	-	ns	2

Notes:

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of VDD/2, and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.

Timing Diagram

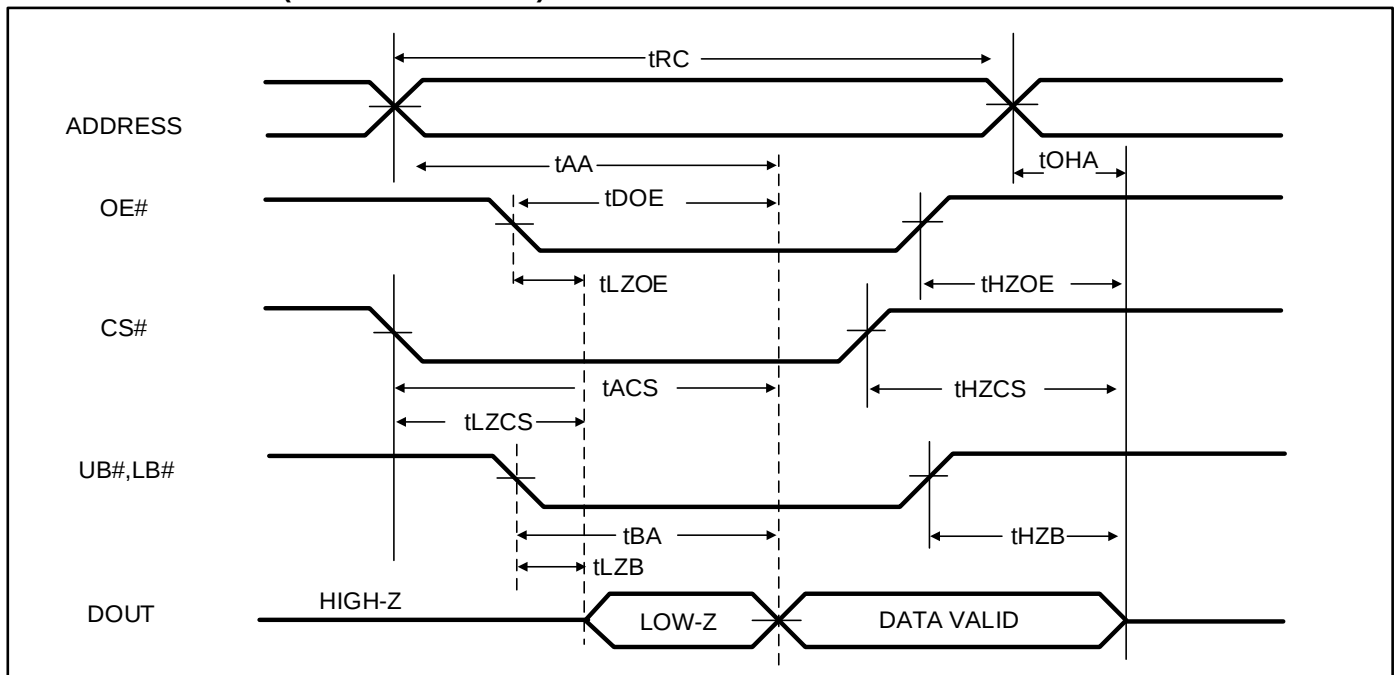
READ CYCLE NO. 1^(1,2) (ADDRESS CONTROLLED , CS#, OE#, UB#, LB# = LOW, WE# = HIGH)



Note:

1. The device is continuously selected.

READ CYCLE NO. 2⁽¹⁾ (OE# CONTROLLED)



Notes:

1. Address is valid prior to or coincident with CS# LOW transition.

IS61WV25616EDALL

WRITE CYCLE AC CHARACTERISTICS

Parameter	Symbol	-20 ⁽¹⁾		unit	notes
		Min	Max		
Write Cycle Time	tWC	20	-	ns	
CS# to Write End	tSCS	12	-	ns	
Address Setup Time to Write End	tAW	12	-	ns	
UB#,LB# to Write End	tPWB	12	-	ns	
Address Hold from Write End	tHA	0	-	ns	
Address Setup Time	tSA	0	-	ns	
WE# Pulse Width	tPWE1	12	-	ns	
WE# Pulse Width (OE# = LOW)	tPWE2	17	-	ns	2
Data Setup to Write End	tSD	9	-	ns	
Data Hold from Write End	tHD	0	-	ns	
WE# LOW to High-Z Output	tHZWE	-	9	ns	
WE# HIGH to Low-Z Output	tLZWE	3	-	ns	

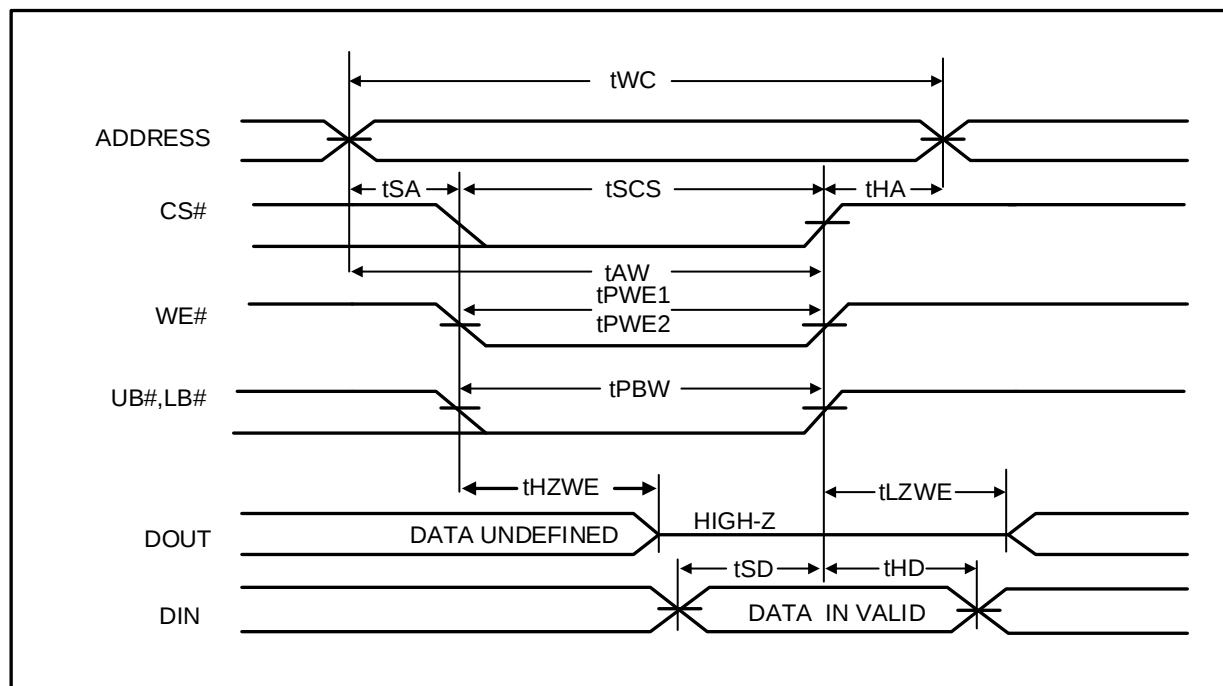
Notes:

- 1 Test conditions assume signal transition times of 3 ns or less, timing reference levels of VDD/2, and output loading specified in Figure 1.
- 2 Tested with the load in Figure 2. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.
- 3 The internal write time is defined by the overlap of CS# = LOW, UB# or LB# = LOW, and WE# = LOW. All signals must be in valid states to initiate a Write, but anyone can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
- 4 If OE# is LOW during write cycle, (WE# controlled, CS# = UB# = LB# = LOW), the minimum Write cycle time for write cycle NO.3 is the sum of tHZWE and tSD

IS61WV25616EDALL

Timing Diagram

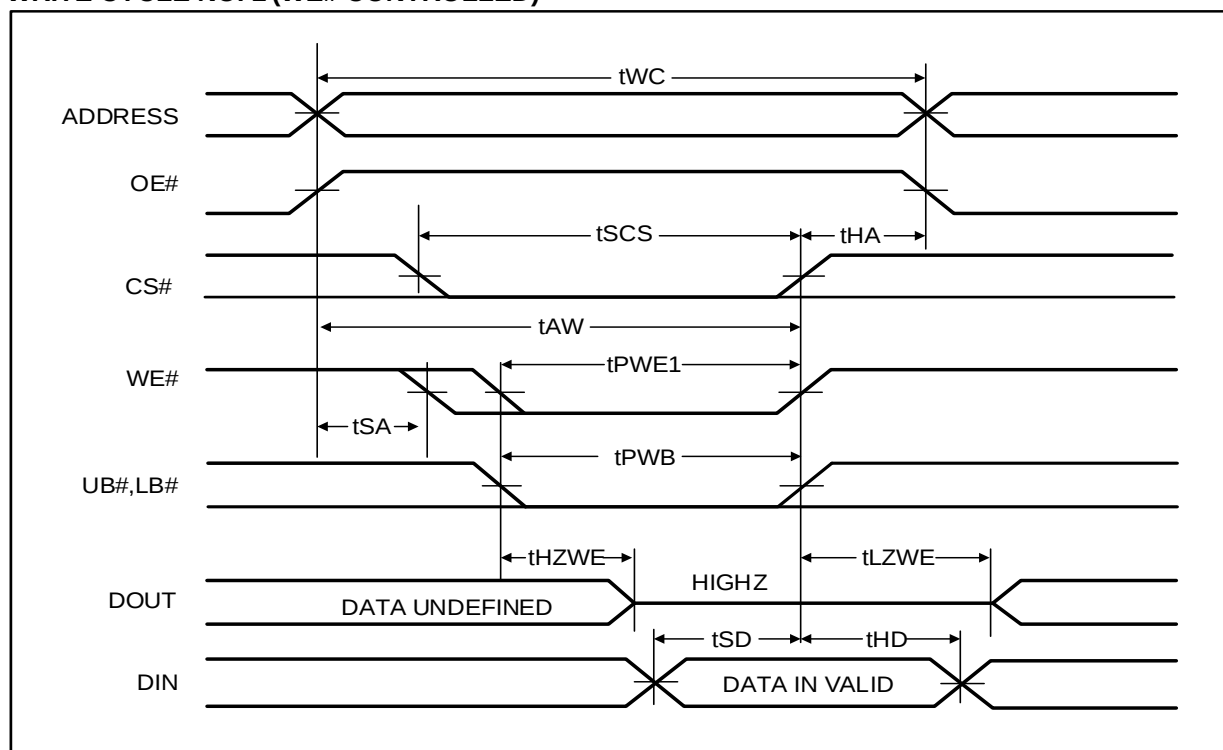
WRITE CYCLE NO. 1⁽¹⁾ (WE# CONTROLLED, OE# = HIGH OR LOW)

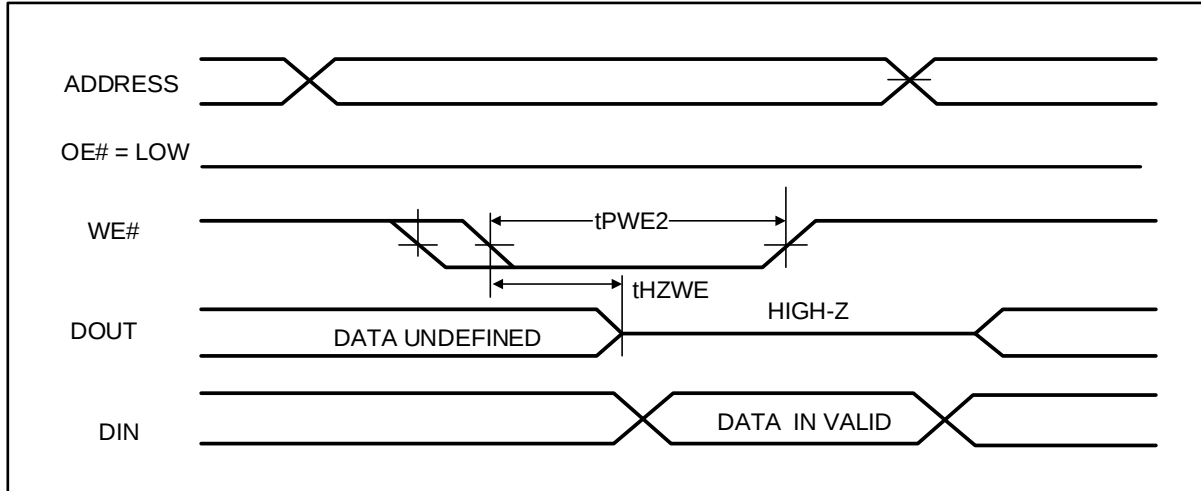
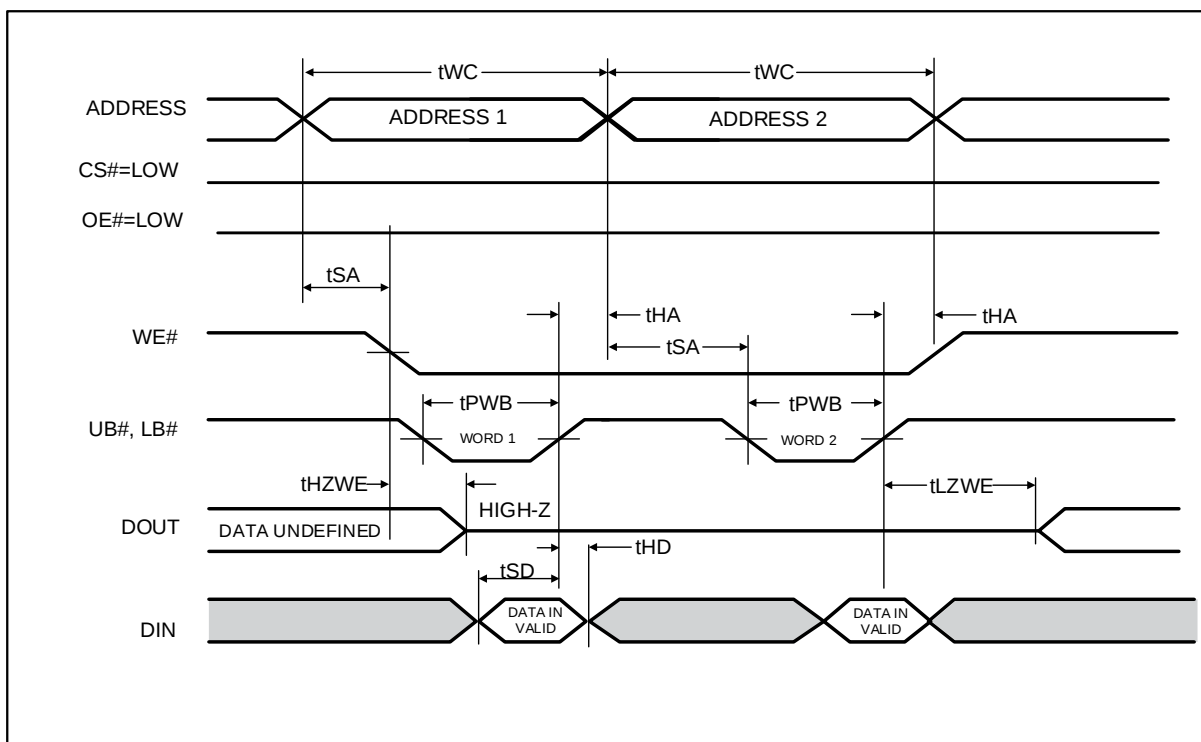


Notes:

1. tHZWE is based on the assumption when tSA=0nS after READ operation. Actual DOUT for tHZWE may not appear if OE# goes high before Write Cycle.

WRITE CYCLE NO. 2 (WE# CONTROLLED)



WRITE CYCLE NO. 3 (WE# CONTROLLED, OE#, CS#, UB #, LB# = LOW)**WRITE CYCLE NO. 4 (UB# & LB# Controlled)**

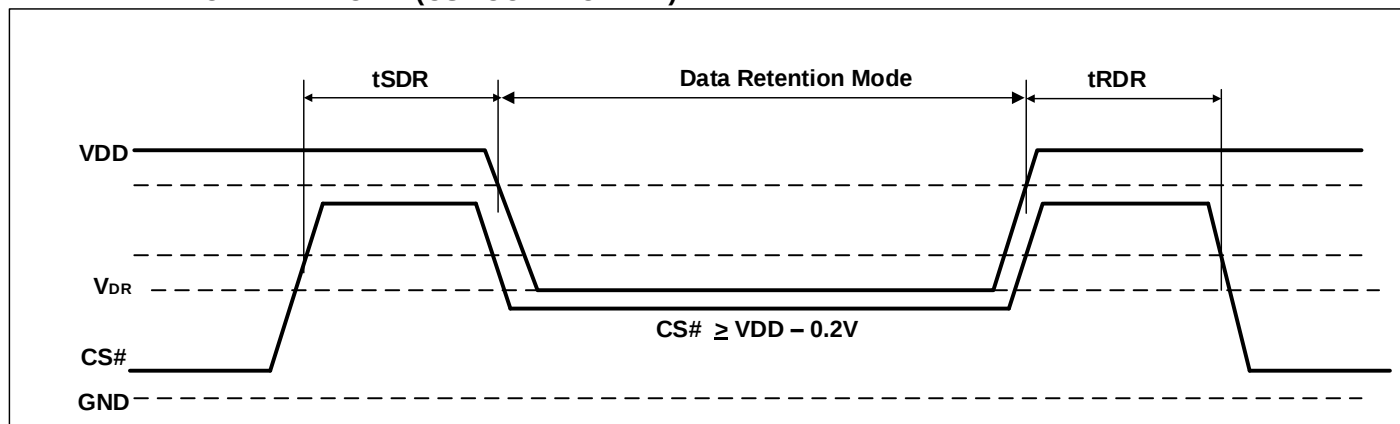
DATA RETENTION CHARACTERISTICS

Symbol	Parameter	Test Condition	OPTION	Min.	Typ. ⁽²⁾	Max.	Unit
V_{DR}	V_{DD} for Data Retention	See Data Retention Waveform		1.2	-	-	V
I_{DR}	Data Retention Current	$V_{DD} = \text{MAX},$ $CS\# \geq V_{DD} - 0.2V,$ $V_{IN} \geq V_{DD} - 0.2V, \text{ or } V_{IN} \leq 0.2V$	Com.	-	0.5	5	mA
			Ind.	-	-	6	
t_{SDR}	Data Retention Setup Time	See Data Retention Waveform		0	-	-	ns
t_{RDR}	Recovery Time	See Data Retention Waveform		t_{RC}	-	-	ns

Notes:

1. If $CS\# > V_{DD} - 0.2V$, all other inputs including $UB\#$ and $LB\#$ must meet this condition.
2. Typical values are measured at $V_{DD} = 1.8V$, $T_A = 25^\circ C$ and not 100% tested.

DATA RETENTION WAVEFORM (CS# CONTROLLED)



ORDERING INFORMATION

Industrial Range: –40°C to +85°C

Speed (ns)	Order Part No.	Package
20	IS61WV25616EDALL-20BI	mini BGA (6mm x 8mm)
20	IS61WV25616EDALL-20BLI	mini BGA (6mm x 8mm), Lead-free
20	IS61WV25616EDALL-20TLI	TSOP (Type II), Lead-free

PACKAGE INFORMATION

